Fig. 2B is a diagram useful in describing the distance between the measurement center of an alignment sensor and the center of an exposure region in a case wherein the present invention is not applied;

Fig. 3 is a diagram showing a region in which an image is formed on a wafer surface in an embodiment of the present invention;

Fig. 4 is a schematic view illustrating a reflection-refraction exposure optical system according to an embodiment of the present invention;

Fig. 5 is a diagram useful in describing general baseline measurement;

Fig. 6 is a diagram showing the structure of an exposure apparatus according to a second embodiment of the present invention;

Fig. 7 is a diagram showing the concept of the reflection-refraction optical system;

Fig. 8 is a diagram showing the concept of an illumination region and a projection region;

Fig. 9A is a diagram showing a reticle area according to the second embodiment;

Fig. 9B is a diagram showing a reticle area to which the present invention is not applied;

Fig. 10A is a diagram showing a wafer area according to the second embodiment;

Fig. 10B is a diagram showing a wafer area to which the present invention is not applied;

Fig. 10C is a diagram showing a wafer area to which the present invention is not applied;

Fig. 11 is a diagram illustrating a system for manufacturing semiconductor devices using an apparatus according to the present invention as seen from a certain viewpoint;